**Product data sheet** 

## 1. General description

Ultrafast, epitaxial rectifier diode in a SOT428 (DPAK) surface-mountable package.

## 2. Features and benefits

- · Low forward voltage drop
- Fast switching
- · Soft recovery characteristic
- · Surface-mountable package
- · High thermal cycling performance
- Low thermal resistance

# 3. Applications

- · High-frequency switched-mode power supplies
- Low loss rectification

## 4. Quick reference data

Table 1. Quick reference data

| Table II Galen     | reference data                      |   |     |      |       |      |
|--------------------|-------------------------------------|---|-----|------|-------|------|
| Symbol             | Parameter                           | Conditions  | Min | Тур  | Max   | Unit |
| $V_R$              | reverse voltage                     | DC  | -   | -    | 200   | V    |
| $V_{RRM}$          | repetitive peak reverse voltage     |   | -   | -    | 200   | V    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2                                      | -   | -    | 8     | Α    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$                              | -   | -    | 80    | Α    |
| Static charact     | eristics                            |   |     |      |       |      |
| V <sub>F</sub>     | forward voltage                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>   | -   | 0.92 | 1.05  | V    |
|                    |                                     | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  | -   | 1.1  | 1.3   | V    |
|                    |                                     | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>  | -   | 8.0  | 0.895 | V    |
| Dynamic char       | acteristics                         |   |     |      |       | •    |
| t <sub>rr</sub>    | reverse recovery time               | $I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/<br>$\mu$ s; $T_j$ = 25 °C; ramp recovery; Fig. 6;<br>Fig. 7; Fig. 8 | -   | 20   | 25    | ns   |
|                    |                                     | step recovery; when switched from $I_F$ = 0.5 A to $I_R$ = 1 A measured at $I_R$ = 0.25 A                         | -   | 15   | 20    | ns   |

# **5. Pinning information**

### **Table 2. Pinning information**

| Pin | Symbol | Description            | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1   | n.c.   | no connection          |                    | K — A          |
| 2   | K      | cathode[1]             | (7 B S)            | 001aaa020      |
| 3   | Α      | anode                  |                    |                |
| mb  | К      | mounting base; cathode | DPAK (SOT428)      |                |

<sup>[1]</sup> it is not possible to make connection with Pin 2 of the SOT428 package

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package |   |         |  |
|-------------|---------|---|---------|--|
|             | Name    | Description   | Version |  |
| BYW29ED-200 | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |  |

# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions  | Min | Max | Unit |
|--------------------|-------------------------------------|---|-----|-----|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |   | -   | 200 | V    |
| $V_{RWM}$          | crest working reverse voltage       |   | -   | 200 | V    |
| V <sub>R</sub>     | reverse voltage                     | DC  | -   | 200 | V    |
| I <sub>F(AV)</sub> | average forward current             | $\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2          | -   | 8   | Α    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $\delta = 0.5 \; ; t_p = 25 \; \mu s; T_{mb} \le 128 \; ^{\circ}C$                    | -   | 16  | Α    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$  | -   | 80  | Α    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$ | -   | 88  | Α    |
| I <sub>RRM</sub>   | repetitive peak reverse current     | $\delta = 0.001 \; ; t_p = 2 \; \mu s$  | -   | 0.2 | Α    |
| I <sub>RSM</sub>   | non-repetitive peak reverse current | t <sub>p</sub> = 100 μs   | -   | 0.2 | Α    |
| T <sub>stg</sub>   | storage temperature                 |   | -40 | 150 | °C   |
| T <sub>j</sub>     | junction temperature                |   | -   | 150 | °C   |
| $V_{ESD}$          | electrostatic discharge voltage     | C = 250 pF; $R$ = 1.5 kΩ; all pins; human body model                                  | -   | 8   | kV   |

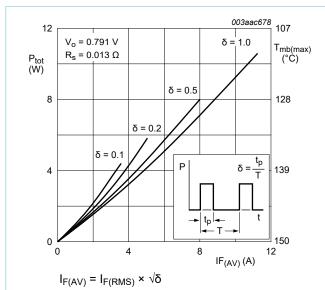


Fig. 1. Total power dissipation and permissible mounting base temperature as a function of average forward current; square waveform; maximum values

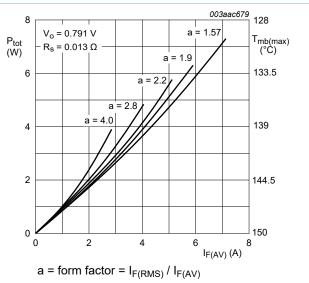


Fig. 2. Total power dissipation and permissible mounting base temperature as a function of average forward current; sinusoidal waveform; maximum values

## 8. Thermal characteristics

### **Table 5. Thermal characteristics**

| Symbol                | Parameter  | Conditions                     |     | Min | Тур | Max | Unit |
|-----------------------|--|--------------------------------|-----|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | with heatsink compound; Fig. 3 |     | -   | -   | 2.7 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient free air | in free air; Fig. 4            | [1] | -   | 50  | -   | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint

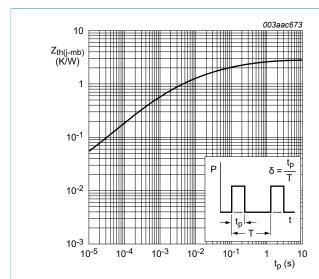


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

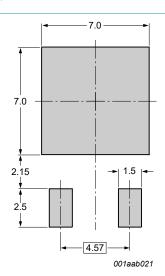
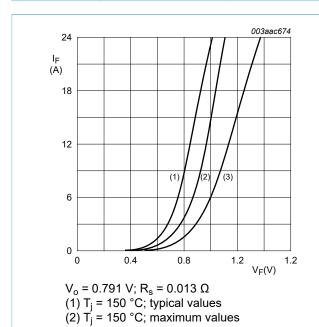


Fig. 4. SOT428: minimum pad sizes for surface-mounting

## 9. Characteristics

**Table 6. Characteristics** 

| Symbol          | Parameter                     | Conditions   | Min | Тур  | Max   | Unit |
|-----------------|-------------------------------|--|-----|------|-------|------|
| Static chara    | acteristics                   |  |     |      |       | _    |
| V <sub>F</sub>  | forward voltage               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>  | -   | 0.92 | 1.05  | V    |
|                 |                               | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>   | -   | 1.1  | 1.3   | V    |
|                 |                               | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>   | -   | 0.8  | 0.895 | V    |
| I <sub>R</sub>  | reverse current               | V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C   | -   | 2    | 10    | μA   |
|                 |                               | V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C  | -   | 0.2  | 0.6   | mA   |
| Dynamic ch      | naracteristics                |  |     |      |       |      |
| t <sub>rr</sub> | reverse recovery time         | $I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/<br>$\mu$ s; $T_j$ = 25 °C; ramp recovery; Fig. 6;<br>Fig. 7; Fig. 8              | -   | 20   | 25    | ns   |
|                 |                               | step recovery; when switched from $I_F$ = 0.5 A to $I_R$ = 1 A measured at $I_R$ = 0.25 A                                      | -   | 15   | 20    | ns   |
| I <sub>RM</sub> | peak reverse recovery current | $I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$ | -   | -    | 1.8   | А    |
| Q <sub>r</sub>  | recovered charge              | $I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 10            | -   | 4    | 11    | nC   |
| $V_{FR}$        | forward recovery voltage      | $I_F = 1 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; Fig. 11   | -   | 1    | -     | V    |



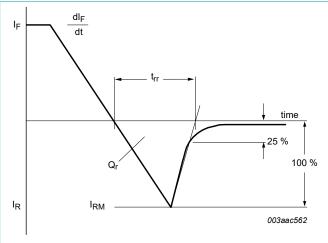


Fig. 6. Reverse recovery definitions; ramp recovery

(3)  $T_i = 25$  °C; maximum values

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### Ultrafast power diode

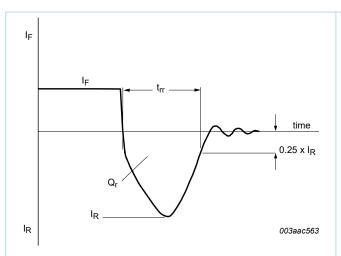


Fig. 7. Reverse recovery definitions; step recovery

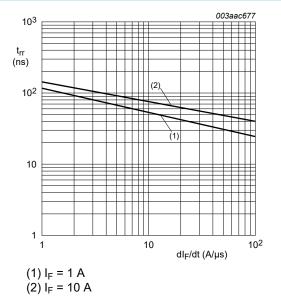


Fig. 8. Reverse recovery time as a function of rate of change of forward current and initial forward current; maximum values

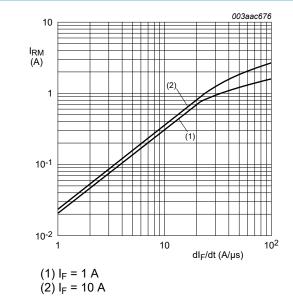
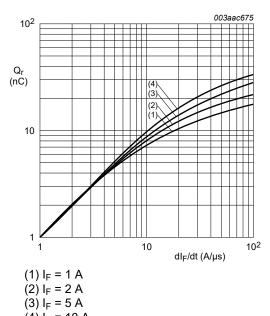


Fig. 9. Peak reverse recovery current as a function of rate of change of forward current and initial forward current; maximum values

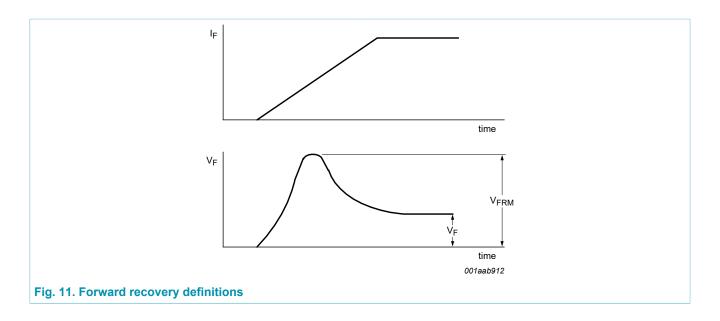


(4)  $I_F = 10 \text{ A}$ Fig. 10. Recovered charge as a function of rate of

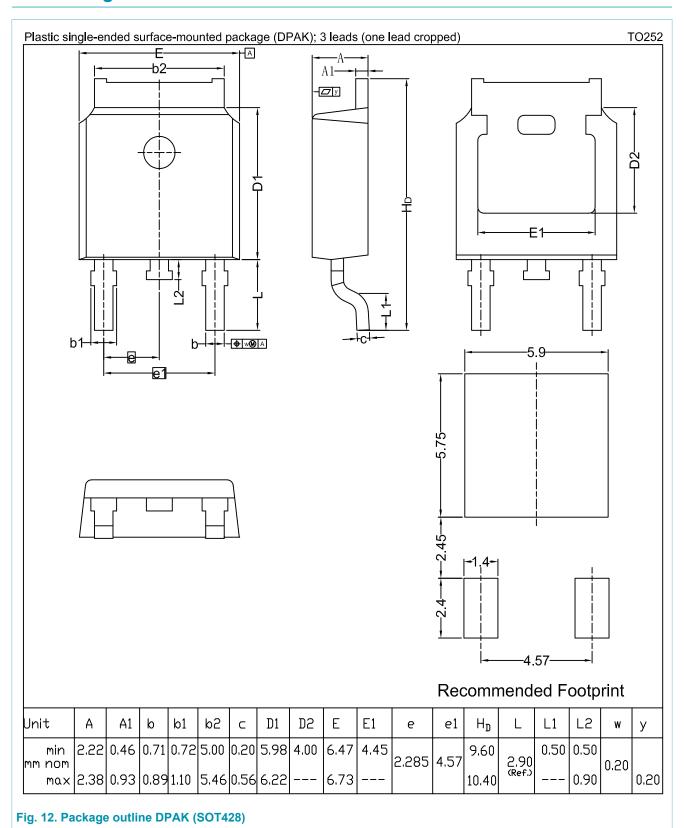
change of forward current; maximum values

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## 10. Package outline



## 11. Legal information

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**BYW29ED-200** 

Ultrafast power diode

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